

74AUP2G240

Low-power dual inverting buffer/line driver; 3-state

Rev. 02 — 22 February 2008

Product data sheet

1. General description

The 74AUP2G240 is a high-performance, low-power, low-voltage, Si-gate CMOS device, superior to most advanced CMOS-compatible TTL families.

Schmitt-trigger action at all inputs makes the circuit tolerant to slower input rise and fall times across the entire V_{CC} range from 0.8 V to 3.6 V.

This device ensures a very low static and dynamic power consumption across the entire V_{CC} range from 0.8 V to 3.6 V.

This device is fully specified for partial Power-down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

The 74AUP2G240 provides the dual inverting buffer/line driver with 3-state output. The 3-state output is controlled by the output enable input (\overline{nOE}). A HIGH level at pin \overline{nOE} causes the output to assume a high-impedance OFF-state.

This device has the input-disable feature, which allows floating input signals. The inputs are disabled when the output enable input \overline{nOE} is HIGH.

2. Features

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
 - ◆ JESD8-12 (0.8 V to 1.3 V)
 - ◆ JESD8-11 (0.9 V to 1.65 V)
 - ◆ JESD8-7 (1.2 V to 1.95 V)
 - ◆ JESD8-5 (1.8 V to 2.7 V)
 - ◆ JESD8-B (2.7 V to 3.6 V)
- ESD protection:
 - ◆ HBM JESD22-A114D Class 3A exceeds 5000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
 - ◆ CDM JESD22-C101C exceeds 1000 V
- Low static power consumption; $I_{CC} = 0.9 \mu\text{A}$ (maximum)
- Latch-up performance exceeds 100 mA per JESD78 Class II
- Inputs accept voltages up to 3.6 V
- Low-noise overshoot and undershoot < 10 % of V_{CC}
- Input-disable feature allows floating input conditions

- I_{OFF} circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C

3. Ordering information

Table 1. Ordering information

Type number	Package			Version
	Temperature range	Name	Description	
74AUP2G240DC	-40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1
74AUP2G240GT	-40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 1 × 1.95 × 0.5 mm	SOT833-1
74AUP2G240GM	-40 °C to +125 °C	XQFN8U	plastic extremely thin quad flat package; no leads; 8 terminals; UTLP based; body 1.6 × 1.6 × 0.5 mm	SOT902-1

4. Marking

Table 2. Marking codes

Type number	Marking code
74AUP2G240DC	p40
74AUP2G240GT	p40
74AUP2G240GM	p40

5. Functional diagram

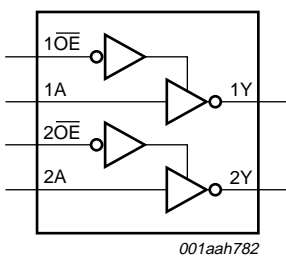


Fig 1. Logic symbol

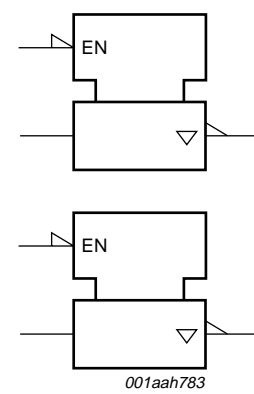


Fig 2. IEC logic symbol

6. Pinning information

6.1 Pinning

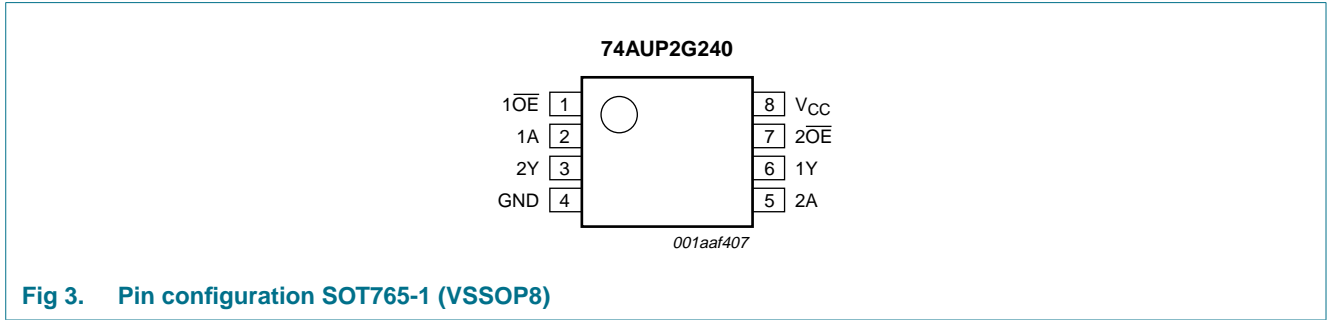


Fig 3. Pin configuration SOT765-1 (VSSOP8)

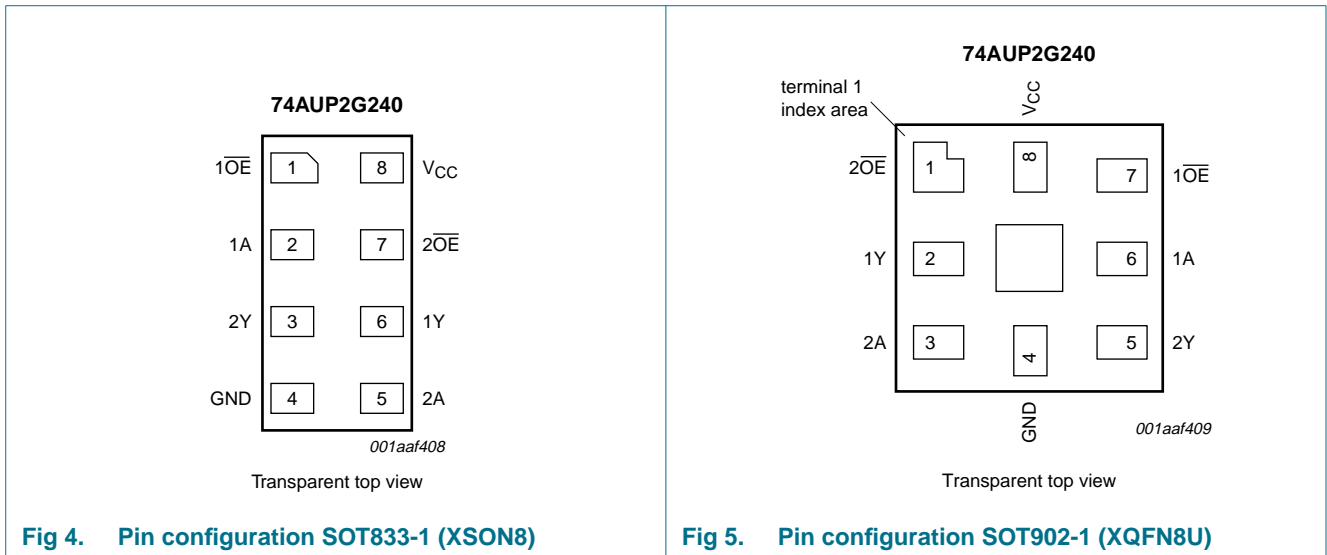


Fig 4. Pin configuration SOT833-1 (XSON8)

Fig 5. Pin configuration SOT902-1 (XQFN8U)

6.2 Pin description

Table 3. Pin description

Symbol	Pin		Description
	SOT765-1, SOT833-1	SOT902-1	
1OE	1	7	output enable input 1OE (active LOW)
1A	2	6	data input 1A
2Y	3	5	data output 2Y
GND	4	4	ground (0 V)
2A	5	3	data input 2A
1Y	6	2	data output 1Y
2OE	7	1	output enable input 2OE (active LOW)
V _{CC}	8	8	supply voltage

7. Functional description

Table 4. Function table^[1]

Input		Output	
nOE	nA	nY	
L	L	H	
L	H	L	
H	X	Z	

- [1] H = HIGH voltage level;
L = LOW voltage level;
X = don't care;
Z = high-impedance OFF-state.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+4.6	V
I _{IK}	input clamping current	V _I < 0 V	-	-50	mA
V _I	input voltage		[1] -0.5	+4.6	V
I _{OK}	output clamping current	V _O > V _{CC} or V _O < 0 V	-	±50	mA
V _O	output voltage	Active mode and Power-down mode	[1] -0.5	+4.6	V
I _O	output current	V _O = 0 V to V _{CC}	-	±20	mA
I _{CC}	supply current		-	50	mA
I _{GND}	ground current		-	-50	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	T _{amb} = -40 °C to +125 °C	[2] -	250	mW

- [1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.
[2] For VSSOP8 packages: above 110 °C the value of P_{tot} derates linearly with 8.0 mW/K.
For XSON8 and XQFN8U packages: above 45 °C the value of P_{tot} derates linearly with 2.4 mW/K.

9. Recommended operating conditions

Table 6. Operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		0.8	3.6	V
V _I	input voltage		0	3.6	V
V _O	output voltage	Active mode	0	V _{CC}	V
		Power-down mode; V _{CC} = 0 V	0	3.6	V
T _{amb}	ambient temperature		-40	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 0.8 V to 3.6 V	0	200	ns/V

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = 25 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	0.70 × V _{CC}	-	-	V
		V _{CC} = 0.9 V to 1.95 V	0.65 × V _{CC}	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	0.30 × V _{CC}	V
		V _{CC} = 0.9 V to 1.95 V	-	-	0.35 × V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = -20 μA; V _{CC} = 0.8 V to 3.6 V	V _{CC} - 0.1	-	-	V
		I _O = -1.1 mA; V _{CC} = 1.1 V	0.75 × V _{CC}	-	-	V
		I _O = -1.7 mA; V _{CC} = 1.4 V	1.11	-	-	V
		I _O = -1.9 mA; V _{CC} = 1.65 V	1.32	-	-	V
		I _O = -2.3 mA; V _{CC} = 2.3 V	2.05	-	-	V
		I _O = -3.1 mA; V _{CC} = 2.3 V	1.9	-	-	V
		I _O = -2.7 mA; V _{CC} = 3.0 V	2.72	-	-	V
		I _O = -4.0 mA; V _{CC} = 3.0 V	2.6	-	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = 20 μA; V _{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	0.3 × V _{CC}	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.31	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.31	V
		I _O = 2.3 mA; V _{CC} = 2.3 V	-	-	0.31	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.44	V
		I _O = 2.7 mA; V _{CC} = 3.0 V	-	-	0.31	V
		I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.44	V
I _I	input leakage current	V _I = GND to 3.6 V; V _{CC} = 0 V to 3.6 V	-	-	±0.1	μA
I _{OZ}	OFF-state output current	V _I = V _{IH} or V _{IL} ; V _O = 0 V to 3.6 V; V _{CC} = 0 V to 3.6 V	-	-	±0.1	μA
I _{OFF}	power-off leakage current	V _I or V _O = 0 V to 3.6 V; V _{CC} = 0 V	-	-	±0.2	μA
ΔI _{OFF}	additional power-off leakage current	V _I or V _O = 0 V to 3.6 V; V _{CC} = 0 V to 0.2 V	-	-	±0.2	μA
I _{CC}	supply current	V _I = GND or V _{CC} ; I _O = 0 A; V _{CC} = 0.8 V to 3.6 V	-	-	0.5	μA

Table 7. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
ΔI_{CC}	additional supply current	data input; $V_I = V_{CC} - 0.6$ V; $I_O = 0$ A; $V_{CC} = 3.3$ V	[1] -	-	40	μ A
		\overline{nOE} input; $V_I = V_{CC} - 0.6$ V; $I_O = 0$ A; $V_{CC} = 3.3$ V	[1] -	-	110	μ A
		disabled inputs; $V_I = \text{GND to } 3.6$ V; $\overline{nOE} = V_{CC}$; $V_{CC} = 0.8$ V to 3.6 V	-	-	1	μ A
C_I	input capacitance	$V_{CC} = 0$ V to 3.6 V; $V_I = \text{GND or } V_{CC}$	-	0.6	-	pF
C_O	output capacitance	output enabled; $V_O = \text{GND}$; $V_{CC} = 0$ V	-	1.7	-	pF
		output disabled; $V_{CC} = 0$ V to 3.6 V; $V_O = \text{GND or } V_{CC}$	-	1.5	-	pF
$T_{amb} = -40$ °C to $+85$ °C						
V_{IH}	HIGH-level input voltage	$V_{CC} = 0.8$ V	$0.70 \times V_{CC}$	-	-	V
		$V_{CC} = 0.9$ V to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		$V_{CC} = 2.3$ V to 2.7 V	1.6	-	-	V
		$V_{CC} = 3.0$ V to 3.6 V	2.0	-	-	V
V_{IL}	LOW-level input voltage	$V_{CC} = 0.8$ V	-	-	$0.30 \times V_{CC}$	V
		$V_{CC} = 0.9$ V to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		$V_{CC} = 2.3$ V to 2.7 V	-	-	0.7	V
		$V_{CC} = 3.0$ V to 3.6 V	-	-	0.9	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = -20$ μ A; $V_{CC} = 0.8$ V to 3.6 V	$V_{CC} - 0.1$	-	-	V
		$I_O = -1.1$ mA; $V_{CC} = 1.1$ V	$0.7 \times V_{CC}$	-	-	V
		$I_O = -1.7$ mA; $V_{CC} = 1.4$ V	1.03	-	-	V
		$I_O = -1.9$ mA; $V_{CC} = 1.65$ V	1.30	-	-	V
		$I_O = -2.3$ mA; $V_{CC} = 2.3$ V	1.97	-	-	V
		$I_O = -3.1$ mA; $V_{CC} = 2.3$ V	1.85	-	-	V
		$I_O = -2.7$ mA; $V_{CC} = 3.0$ V	2.67	-	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = 20$ μ A; $V_{CC} = 0.8$ V to 3.6 V	-	-	0.1	V
		$I_O = 1.1$ mA; $V_{CC} = 1.1$ V	-	-	$0.3 \times V_{CC}$	V
		$I_O = 1.7$ mA; $V_{CC} = 1.4$ V	-	-	0.37	V
		$I_O = 1.9$ mA; $V_{CC} = 1.65$ V	-	-	0.35	V
		$I_O = 2.3$ mA; $V_{CC} = 2.3$ V	-	-	0.33	V
		$I_O = 3.1$ mA; $V_{CC} = 2.3$ V	-	-	0.45	V
		$I_O = 2.7$ mA; $V_{CC} = 3.0$ V	-	-	0.33	V
I_I	input leakage current	$V_I = \text{GND to } 3.6$ V; $V_{CC} = 0$ V to 3.6 V	-	-	± 0.5	μ A
		$V_I = V_{IH}$ or V_{IL} ; $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	± 0.5	μ A
I_{OFF}	power-off leakage current	V_I or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	± 0.5	μ A

Table 7. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
ΔI_{OFF}	additional power-off leakage current	V_I or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	± 0.6	μ A
I_{CC}	supply current	$V_I = \text{GND}$ or V_{CC} ; $I_O = 0$ A; $V_{CC} = 0.8$ V to 3.6 V	-	-	0.9	μ A
ΔI_{CC}	additional supply current	data input; $V_I = V_{CC} - 0.6$ V; $I_O = 0$ A; $V_{CC} = 3.3$ V	[1] -	-	50	μ A
		\overline{nOE} input; $V_I = V_{CC} - 0.6$ V; $I_O = 0$ A; $V_{CC} = 3.3$ V	[1] -	-	120	μ A
		disabled inputs; $V_I = \text{GND}$ to 3.6 V; $\overline{nOE} = V_{CC}$; $V_{CC} = 0.8$ V to 3.6 V	-	-	1	μ A
$T_{amb} = -40$ °C to $+125$ °C						
V_{IH}	HIGH-level input voltage	$V_{CC} = 0.8$ V	$0.75 \times V_{CC}$	-	-	V
		$V_{CC} = 0.9$ V to 1.95 V	$0.70 \times V_{CC}$	-	-	V
		$V_{CC} = 2.3$ V to 2.7 V	1.6	-	-	V
		$V_{CC} = 3.0$ V to 3.6 V	2.0	-	-	V
V_{IL}	LOW-level input voltage	$V_{CC} = 0.8$ V	-	-	$0.25 \times V_{CC}$	V
		$V_{CC} = 0.9$ V to 1.95 V	-	-	$0.30 \times V_{CC}$	V
		$V_{CC} = 2.3$ V to 2.7 V	-	-	0.7	V
		$V_{CC} = 3.0$ V to 3.6 V	-	-	0.9	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = -20$ μ A; $V_{CC} = 0.8$ V to 3.6 V	$V_{CC} - 0.11$	-	-	V
		$I_O = -1.1$ mA; $V_{CC} = 1.1$ V	$0.6 \times V_{CC}$	-	-	V
		$I_O = -1.7$ mA; $V_{CC} = 1.4$ V	0.93	-	-	V
		$I_O = -1.9$ mA; $V_{CC} = 1.65$ V	1.17	-	-	V
		$I_O = -2.3$ mA; $V_{CC} = 2.3$ V	1.77	-	-	V
		$I_O = -3.1$ mA; $V_{CC} = 2.3$ V	1.67	-	-	V
		$I_O = -2.7$ mA; $V_{CC} = 3.0$ V	2.40	-	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = 20$ μ A; $V_{CC} = 0.8$ V to 3.6 V	-	-	0.11	V
		$I_O = 1.1$ mA; $V_{CC} = 1.1$ V	-	-	$0.33 \times V_{CC}$	V
		$I_O = 1.7$ mA; $V_{CC} = 1.4$ V	-	-	0.41	V
		$I_O = 1.9$ mA; $V_{CC} = 1.65$ V	-	-	0.39	V
		$I_O = 2.3$ mA; $V_{CC} = 2.3$ V	-	-	0.36	V
		$I_O = 3.1$ mA; $V_{CC} = 2.3$ V	-	-	0.50	V
		$I_O = 2.7$ mA; $V_{CC} = 3.0$ V	-	-	0.36	V
I_I	input leakage current	$V_I = \text{GND}$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	± 0.75	μ A
		$V_I = V_{IH}$ or V_{IL} ; $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	± 0.75	μ A
I_{OFF}	power-off leakage current	V_I or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	± 0.75	μ A

Table 7. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
ΔI_{OFF}	additional power-off leakage current	V_I or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	± 0.75	μA
I_{CC}	supply current	$V_I = GND$ or V_{CC} ; $I_O = 0$ A; $V_{CC} = 0.8$ V to 3.6 V	-	-	1.4	μA
ΔI_{CC}	additional supply current	data input; $V_I = V_{CC} - 0.6$ V; $I_O = 0$ A; $V_{CC} = 3.3$ V	[1]	-	75	μA
		\overline{nOE} input; $V_I = V_{CC} - 0.6$ V; $I_O = 0$ A; $V_{CC} = 3.3$ V	[1]	-	180	μA
		disabled inputs; $V_I = GND$ to 3.6 V; $\overline{nOE} = V_{CC}$; $V_{CC} = 0.8$ V to 3.6 V	-	-	1	μA

[1] One input at $V_{CC} - 0.6$ V, other input at V_{CC} or GND.

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V; for test circuit see [Figure 8](#)).

Symbol	Parameter	Conditions	25 °C			-40 °C to +125 °C			Unit
			Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
$C_L = 5$ pF									
t_{pd}	propagation delay	nA to nY ; see Figure 6 [2]							
		$V_{CC} = 0.8$ V	-	22.3	-	-	-	-	ns
		$V_{CC} = 1.1$ V to 1.3 V	3.0	5.8	12.6	2.8	14.1	15.5	ns
		$V_{CC} = 1.4$ V to 1.6 V	2.3	4.0	7.3	2.1	8.5	9.4	ns
		$V_{CC} = 1.65$ V to 1.95 V	2.0	3.2	5.5	1.9	6.7	7.4	ns
		$V_{CC} = 2.3$ V to 2.7 V	1.8	2.6	4.1	1.5	4.8	5.3	ns
t_{en}	enable time	\overline{nOE} to nY ; see Figure 7 [3]							
		$V_{CC} = 0.8$ V	-	70.2	-	-	-	-	ns
		$V_{CC} = 1.1$ V to 1.3 V	3.1	6.4	14.3	2.8	15.9	17.5	ns
		$V_{CC} = 1.4$ V to 1.6 V	2.5	4.4	8.1	2.2	9.5	10.5	ns
		$V_{CC} = 1.65$ V to 1.95 V	2.1	3.6	6.2	1.9	7.4	8.2	ns
		$V_{CC} = 2.3$ V to 2.7 V	1.8	2.8	4.6	1.7	5.4	6.0	ns
t_{dis}	disable time	\overline{nOE} to nY ; see Figure 7 [4]							
		$V_{CC} = 0.8$ V	-	14.8	-	-	-	-	ns
		$V_{CC} = 1.1$ V to 1.3 V	2.0	4.3	7.4	2.3	8.3	9.2	ns
		$V_{CC} = 1.4$ V to 1.6 V	1.6	3.2	5.2	1.7	5.9	6.5	ns
		$V_{CC} = 1.65$ V to 1.95 V	1.5	3.0	4.8	1.5	5.5	6.1	ns
		$V_{CC} = 2.3$ V to 2.7 V	1.1	2.2	3.5	1.4	4.0	4.5	ns
t_{dis}	disable time	$V_{CC} = 3.0$ V to 3.6 V	1.3	2.5	3.9	1.4	4.5	5.0	ns

Table 8. Dynamic characteristics ...continued
 Voltages are referenced to GND (ground = 0 V; for test circuit see [Figure 8](#).

Symbol	Parameter	Conditions	25 °C			–40 °C to +125 °C			Unit
			Min	Typ ^[1]	Max	Min	Max (85 °C)	Max (125 °C)	
C_L = 10 pF									
t _{pd}	propagation delay	nA to nY; see Figure 6	[2]						
		V _{CC} = 0.8 V	-	25.7	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	3.5	6.6	14.5	3.2	16.3	18.0	ns
		V _{CC} = 1.4 V to 1.6 V	2.2	4.6	8.4	2.0	9.9	10.9	ns
		V _{CC} = 1.65 V to 1.95 V	2.0	3.8	6.4	1.8	7.7	8.6	ns
		V _{CC} = 2.3 V to 2.7 V	1.8	3.1	4.8	1.7	5.7	6.4	ns
		V _{CC} = 3.0 V to 3.6 V	1.7	2.8	4.3	1.7	5.0	5.5	ns
t _{en}	enable time	nOE to nY; see Figure 7	[3]						
		V _{CC} = 0.8 V	-	74.0	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	3.6	7.4	16.3	3.2	18.2	20.1	ns
		V _{CC} = 1.4 V to 1.6 V	2.3	5.1	9.2	2.1	10.9	12.0	ns
		V _{CC} = 1.65 V to 1.95 V	2.0	4.1	7.1	1.8	8.5	9.4	ns
		V _{CC} = 2.3 V to 2.7 V	1.8	3.4	5.4	1.7	6.4	7.1	ns
		V _{CC} = 3.0 V to 3.6 V	1.8	3.1	4.8	1.7	5.7	6.3	ns
t _{dis}	disable time	nOE to nY; see Figure 7	[4]						
		V _{CC} = 0.8 V	-	33.7	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	3.4	5.4	9.0	3.2	10.0	11.0	ns
		V _{CC} = 1.4 V to 1.6 V	2.1	4.1	6.3	2.1	7.1	7.9	ns
		V _{CC} = 1.65 V to 1.95 V	2.3	4.2	6.3	1.8	7.1	7.9	ns
		V _{CC} = 2.3 V to 2.7 V	1.6	3.0	4.6	1.7	5.2	5.7	ns
		V _{CC} = 3.0 V to 3.6 V	2.1	3.8	5.7	1.7	6.4	7.1	ns
C_L = 15 pF									
t _{pd}	propagation delay	nA to nY; see Figure 6	[2]						
		V _{CC} = 0.8 V	-	29.0	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	3.9	7.4	16.3	3.6	18.4	20.2	ns
		V _{CC} = 1.4 V to 1.6 V	3.0	5.1	9.4	2.5	11.1	12.3	ns
		V _{CC} = 1.65 V to 1.95 V	2.2	4.2	7.2	2.1	8.7	9.6	ns
		V _{CC} = 2.3 V to 2.7 V	2.0	3.5	5.4	1.9	6.5	7.2	ns
		V _{CC} = 3.0 V to 3.6 V	2.0	3.3	4.9	1.9	5.7	6.4	ns
t _{en}	enable time	nOE to nY; see Figure 7	[3]						
		V _{CC} = 0.8 V	-	77.8	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	4.0	8.2	18.2	3.6	20.4	22.5	ns
		V _{CC} = 1.4 V to 1.6 V	3.0	5.6	10.3	2.5	12.2	13.4	ns
		V _{CC} = 1.65 V to 1.95 V	2.3	4.6	7.9	2.1	9.5	10.5	ns
		V _{CC} = 2.3 V to 2.7 V	2.1	3.9	6.0	2.0	7.2	7.9	ns
		V _{CC} = 3.0 V to 3.6 V	2.1	3.6	5.5	1.9	6.4	7.1	ns

Table 8. Dynamic characteristics ...continuedVoltages are referenced to GND (ground = 0 V; for test circuit see [Figure 8](#)).

Symbol	Parameter	Conditions	25 °C			–40 °C to +125 °C			Unit
			Min	Typ ^[1]	Max	Min	Max (85 °C)	Max (125 °C)	
t _{dis}	disable time	n $\overline{\text{OE}}$ to nY; see Figure 7 ^[4]							
		V _{CC} = 0.8 V	-	62.5	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	4.3	6.6	10.4	3.6	11.6	12.8	ns
		V _{CC} = 1.4 V to 1.6 V	3.0	5.0	7.4	2.5	8.4	9.3	ns
		V _{CC} = 1.65 V to 1.95 V	3.0	5.3	7.8	2.1	8.7	9.7	ns
		V _{CC} = 2.3 V to 2.7 V	2.1	3.8	5.7	2.0	6.4	7.1	ns
		V _{CC} = 3.0 V to 3.6 V	2.9	5.0	7.4	1.9	8.3	9.1	ns
C_L = 30 pF									
t _{pd}	propagation delay	nA to nY; see Figure 6 ^[2]							
		V _{CC} = 0.8 V	-	39.1	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	5.0	9.7	21.6	4.6	24.3	26.8	ns
		V _{CC} = 1.4 V to 1.6 V	4.0	6.7	12.3	3.0	14.6	16.1	ns
		V _{CC} = 1.65 V to 1.95 V	2.9	5.5	9.5	2.7	11.5	12.6	ns
		V _{CC} = 2.3 V to 2.7 V	2.7	4.6	7.1	2.5	8.6	9.5	ns
		V _{CC} = 3.0 V to 3.6 V	2.6	4.3	6.4	2.5	7.7	8.5	ns
t _{en}	enable time	n $\overline{\text{OE}}$ to nY; see Figure 7 ^[3]							
		V _{CC} = 0.8 V	-	89.4	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	5.2	10.6	23.8	4.6	26.7	29.5	ns
		V _{CC} = 1.4 V to 1.6 V	4.0	7.3	13.2	3.0	15.7	17.4	ns
		V _{CC} = 1.65 V to 1.95 V	3.0	6.0	10.2	2.7	12.3	13.6	ns
		V _{CC} = 2.3 V to 2.7 V	2.8	5.0	7.8	2.6	9.3	10.3	ns
		V _{CC} = 3.0 V to 3.6 V	2.8	4.8	7.1	2.6	8.4	9.3	ns
t _{dis}	disable time	n $\overline{\text{OE}}$ to nY; see Figure 7 ^[4]							
		V _{CC} = 0.8 V	-	68.9	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	6.0	9.3	15.0	4.6	16.5	18.2	ns
		V _{CC} = 1.4 V to 1.6 V	4.4	7.7	11.0	3.0	12.2	13.4	ns
		V _{CC} = 1.65 V to 1.95 V	5.1	8.8	12.4	2.7	13.7	15.1	ns
		V _{CC} = 2.3 V to 2.7 V	3.6	6.2	9.0	2.6	10.0	11.0	ns
		V _{CC} = 3.0 V to 3.6 V	5.2	8.8	12.7	2.6	14.0	15.4	ns

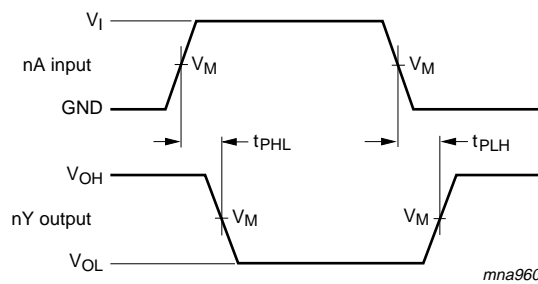
Table 8. Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V; for test circuit see [Figure 8](#)).

Symbol	Parameter	Conditions	25 °C			-40 °C to +125 °C			Unit
			Min	Typ ^[1]	Max	Min	Max (85 °C)	Max (125 °C)	
C_L = 5 pF, 10 pF, 15 pF and 30 pF									
C _{PD}	power dissipation capacitance	f = 1 MHz; V _I = GND to V _{CC} ^[5]							
		V _{CC} = 0.8 V	-	2.7	-	-	-	-	pF
		V _{CC} = 1.1 V to 1.3 V	-	2.9	-	-	-	-	pF
		V _{CC} = 1.4 V to 1.6 V	-	3.0	-	-	-	-	pF
		V _{CC} = 1.65 V to 1.95 V	-	3.2	-	-	-	-	pF
		V _{CC} = 2.3 V to 2.7 V	-	3.7	-	-	-	-	pF
		V _{CC} = 3.0 V to 3.6 V	-	4.2	-	-	-	-	pF

- [1] All typical values are measured at nominal V_{CC}.
- [2] t_{pd} is the same as t_{PLH} and t_{PHL}.
- [3] t_{en} is the same as t_{PZH} and t_{PZL}.
- [4] t_{dis} is the same as t_{PHZ} and t_{PLZ}.
- [5] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).
 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:
 f_i = input frequency in MHz;
 f_o = output frequency in MHz;
 C_L = output load capacitance in pF;
 V_{CC} = supply voltage in V;
 N = number of inputs switching;
 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

12. Waveforms

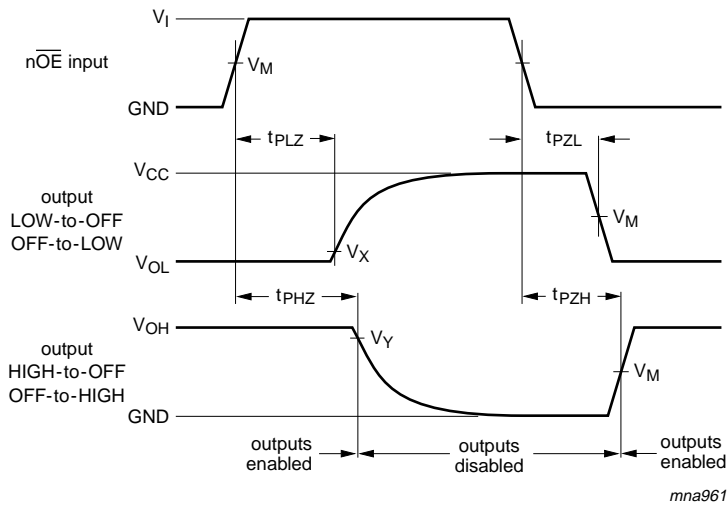


Measurement points are given in [Table 9](#).
 Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 6. The data input (nA) to output (nY) propagation delays

Table 9. Measurement points

Supply voltage	Output	Input		
V _{CC}	V _M	V _M	V _I	t _r = t _f
0.8 V to 3.6 V	0.5 × V _{CC}	0.5 × V _{CC}	V _{CC}	≤ 3.0 ns



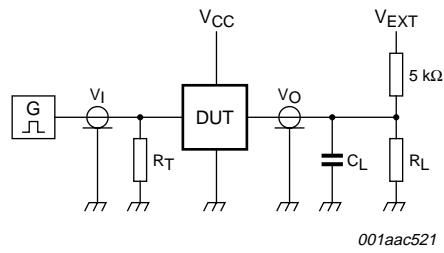
Measurement points are given in [Table 10](#).

Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 7. 3-state enable and disable times

Table 10. Measurement points

Supply voltage	Input	Output		
V_{CC}	V_M	V_M	V_X	V_Y
0.8 V to 1.6 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	$V_{OL} + 0.1 \text{ V}$	$V_{OH} - 0.1 \text{ V}$
1.65 V to 2.7 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	$V_{OL} + 0.15 \text{ V}$	$V_{OH} - 0.15 \text{ V}$
3.0 V to 3.6 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	$V_{OL} + 0.3 \text{ V}$	$V_{OH} - 0.3 \text{ V}$



001aac521

Test data is given in [Table 11](#).

Definitions for test circuit:

R_L = Load resistance.

C_L = Load capacitance including jig and probe capacitance.

R_T = Termination resistance should be equal to the output impedance Z_o of the pulse generator.

V_{EXT} = External voltage for measuring switching times.

Fig 8. Load circuitry for switching times

Table 11. Test data

Supply voltage	Load		V_{EXT}		
V_{CC}	C_L	R_L [1]	t_{PLH} , t_{PHL}	t_{PZH} , t_{PHZ}	t_{PZL} , t_{PLZ}
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 kΩ or 1 MΩ	open	GND	$2 \times V_{CC}$

[1] For measuring enable and disable times $R_L = 5 \text{ k}\Omega$, for measuring propagation delays, setup and hold times and pulse width $R_L = 1 \text{ M}\Omega$.

13. Package outline

VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1

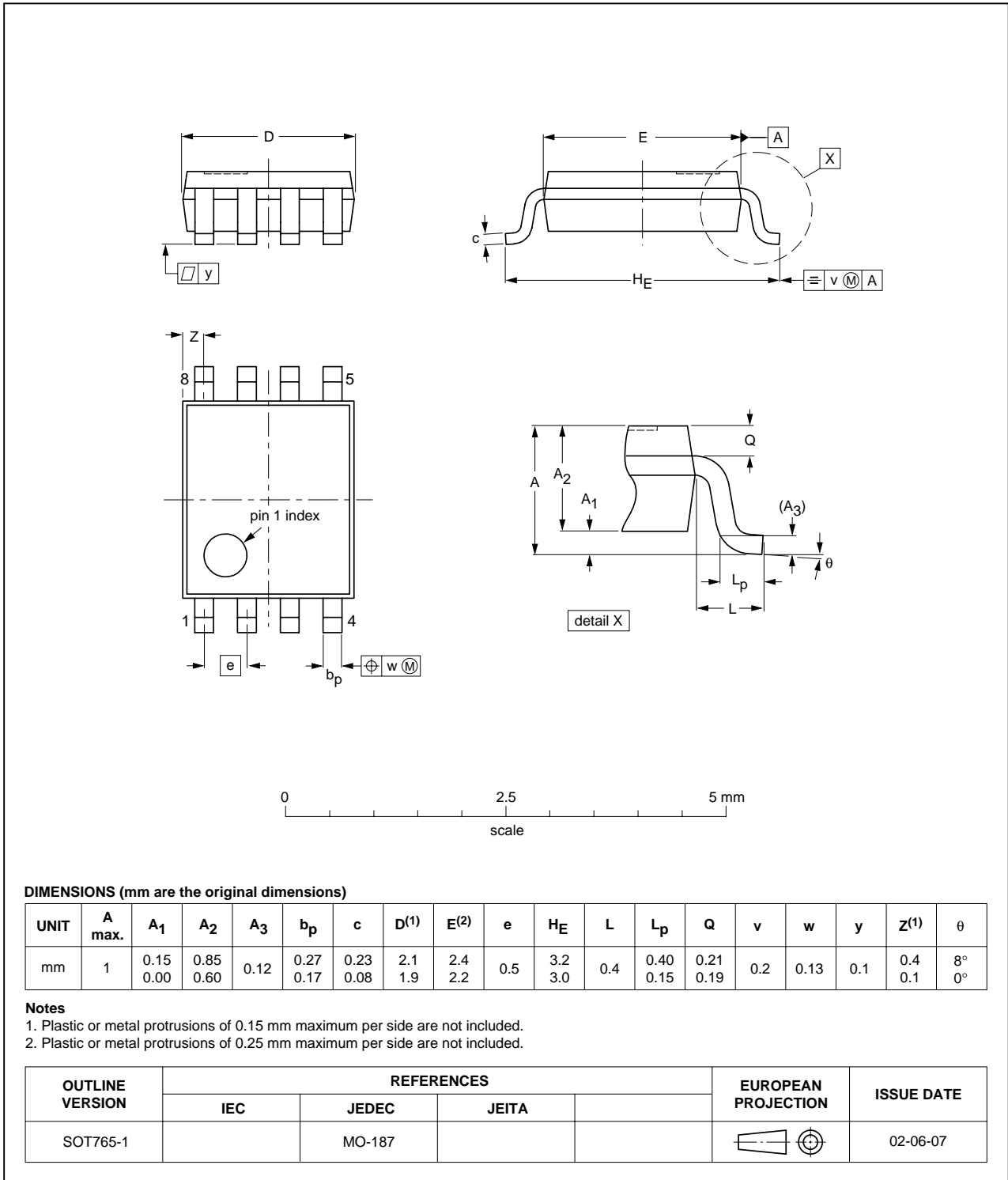


Fig 9. Package outline SOT765-1 (VSSOP8)

XSON8: plastic extremely thin small outline package; no leads; 8 terminals; body 1 x 1.95 x 0.5 mm

SOT833-1

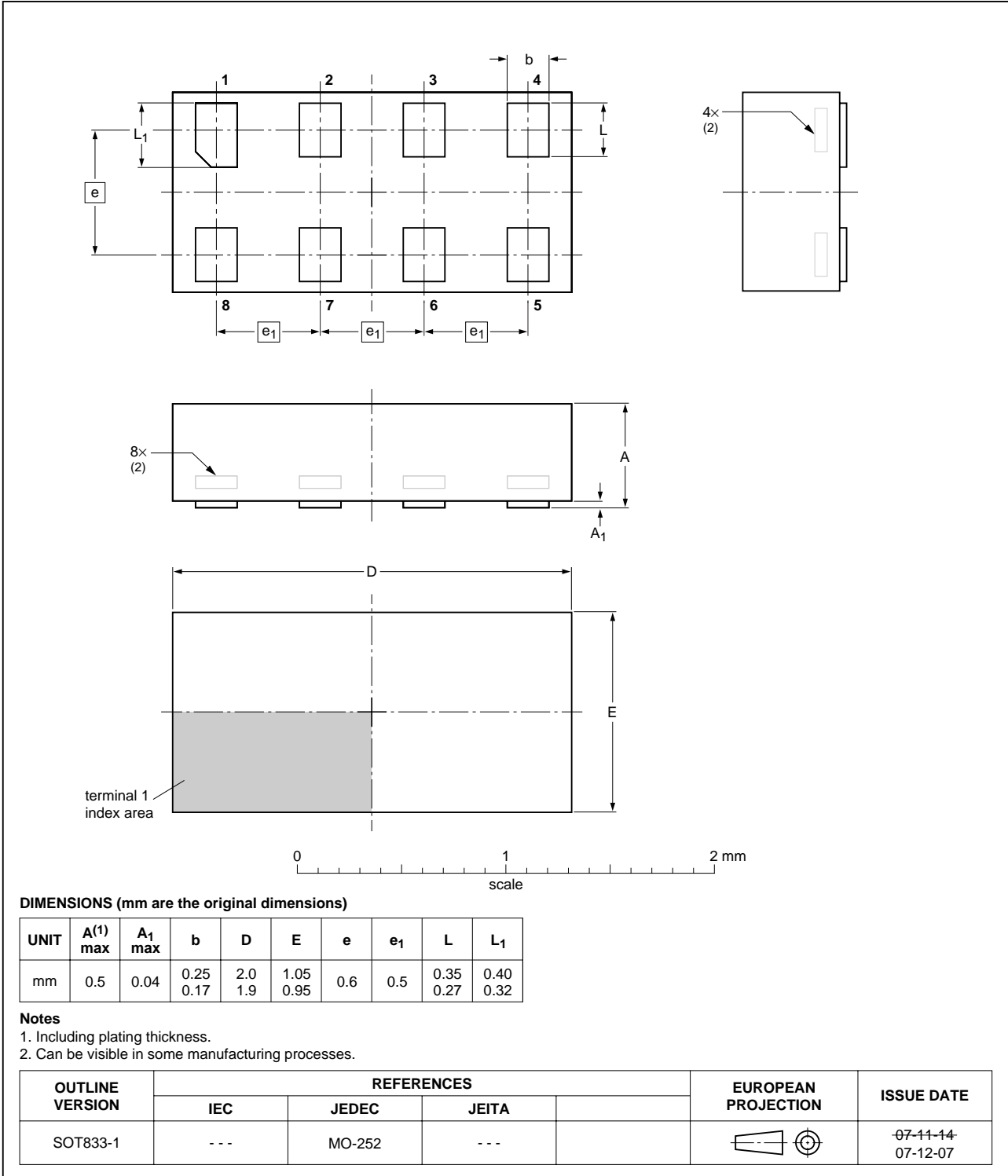


Fig 10. Package outline SOT833-1 (XSON8)

XQFN8U: plastic extremely thin quad flat package; no leads; 8 terminals; UTLP based; body 1.6 x 1.6 x 0.5 mm

SOT902-1

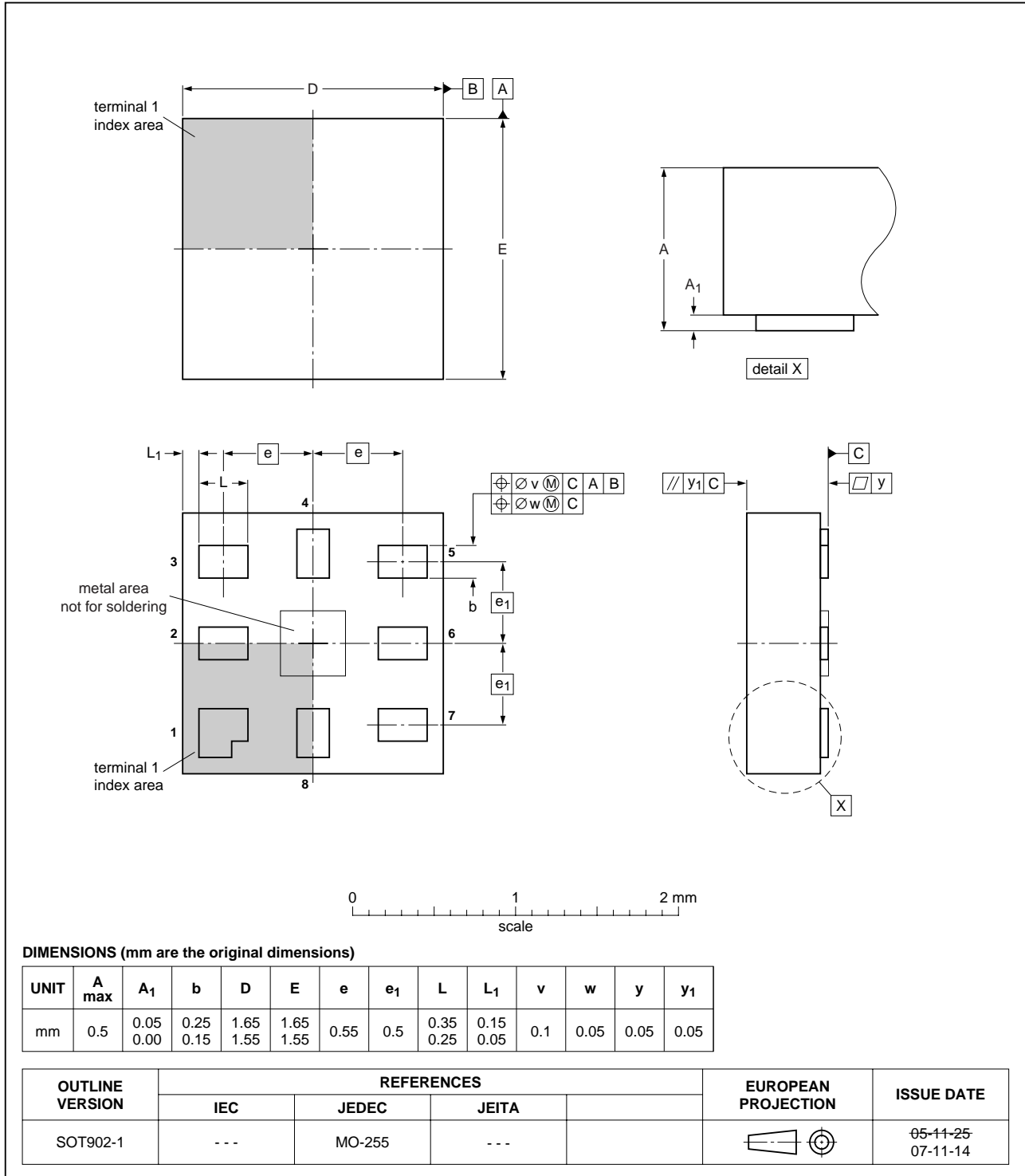


Fig 11. Package outline SOT902-1 (XQFN8U)

14. Abbreviations

Table 12. Abbreviations

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

15. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP2G240_2	20080222	Product data sheet	-	74AUP2G240_1
Modifications:		<ul style="list-style-type: none">• Figure 1 and Figure 2: pin numbers removed• Figure 11: package outline drawing updated to latest version		
74AUP2G240_1	20061006	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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